



### P-Channel 1.8-V (G-S) MOSFET

#### CHARACTERISTICS

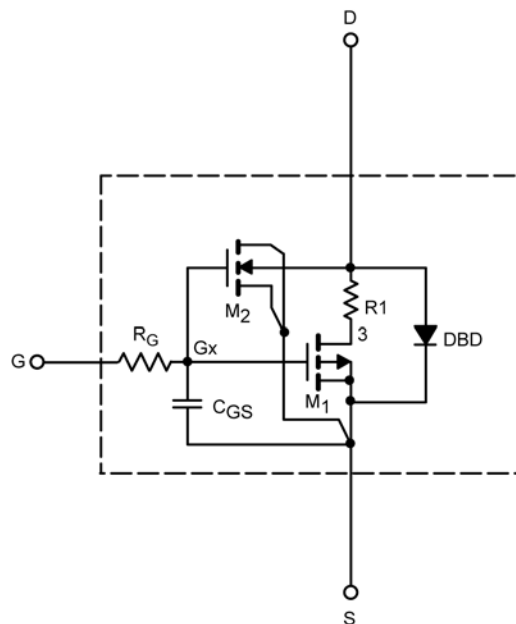
- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

#### DESCRIPTION

The attached spice model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 to 125°C temperature ranges under the pulsed 0-V to 5-V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

#### SUBCIRCUIT MODEL SCHEMATIC



This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.



SPECIFICATIONS ( $T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	Test Condition	Simulated Data	Measured Data	Unit
<b>Static</b>					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	0.61		V
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	410		A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = -4.5 \text{ V}, I_D = -14 \text{ A}$	0.0074	0.0075	$\Omega$
		$V_{GS} = -2.5 \text{ V}, I_D = -12 \text{ A}$	0.0092	0.0092	
		$V_{GS} = -1.8 \text{ V}, I_D = -10 \text{ A}$	0.012	0.013	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -10 \text{ V}, I_D = -14 \text{ A}$	43	58	S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -2.1 \text{ A}$	-0.82	-0.57	V
<b>Dynamic<sup>b</sup></b>					
Total Gate Charge	$Q_g$	$V_{DS} = -4 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -14 \text{ A}$	49	55	nC
Gate-Source Charge	$Q_{gs}$		6	6	
Gate-Drain Charge	$Q_{gd}$		10	10	

Notes

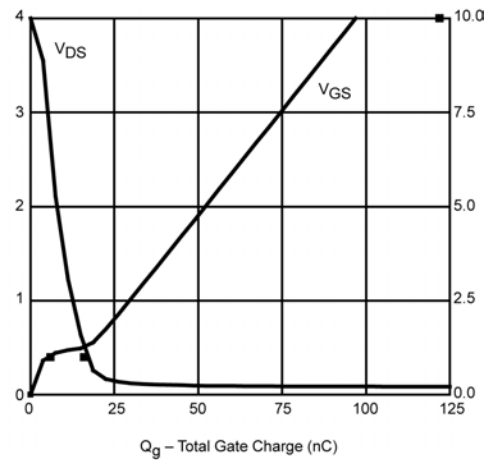
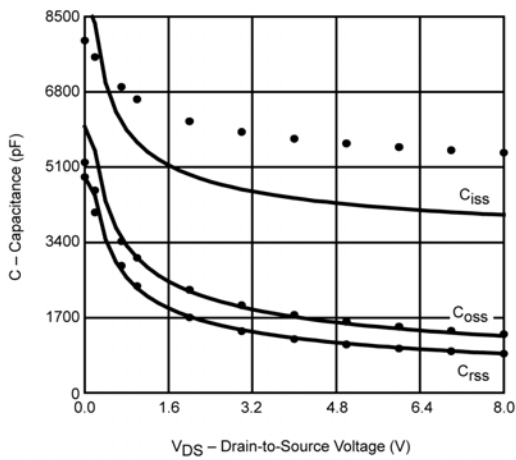
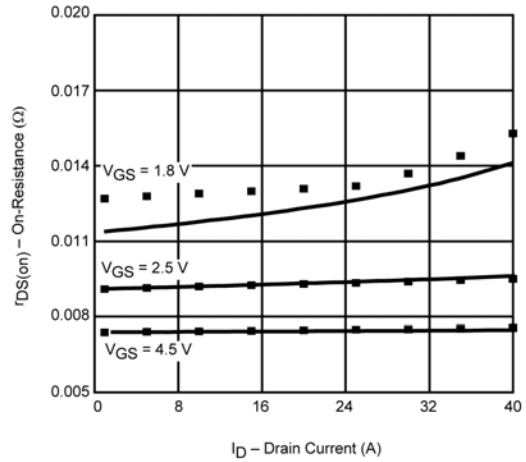
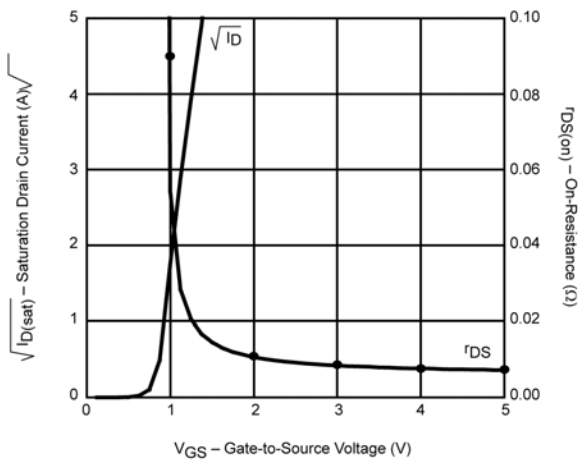
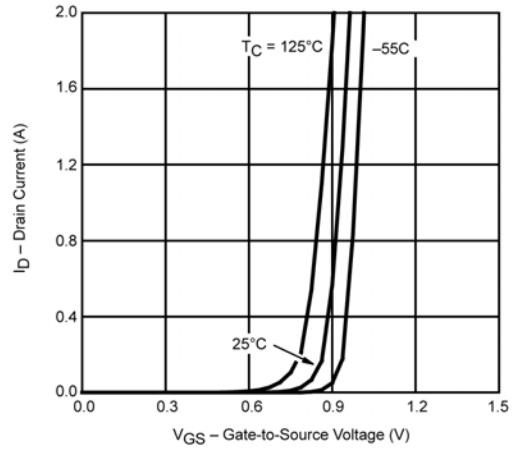
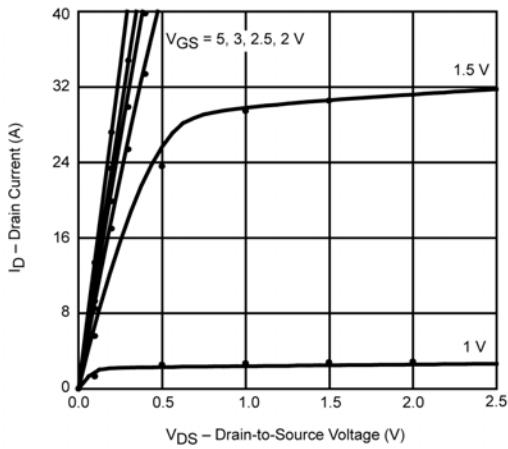
- a. Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.



# SPICE Device Model Si4465ADY

## Vishay Siliconix

COMPARISON OF MODEL WITH MEASURED DATA ( $T_J=25^\circ\text{C}$  UNLESS OTHERWISE NOTED)



Note: Dots and squares represent measured data.



## Disclaimer

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